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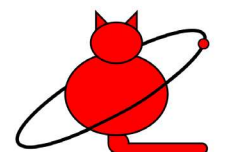
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Advanced CMOS Modeling

Date: Tuesday, September 20, 2022
Time: 17:30 - 18:30
Room: Aula 1D
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Viktor Sverdlov, TU Wien

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Room: Aula 1F
Chair(s): Denis Rideau, STMicroelectronics
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Reliability & Characterization

Date: Tuesday, September 20, 2022
Time: 9:20 - 10:40
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Room: Aula 1F

Chair(s): Jean-Michel Sallese, EPFL
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Frederic Allibert, SOITEC, France

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Date: Wednesday, September 21, 2022

Time: 15:20 - 16:40

Room: Aula 1F

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Jens Trommer, NamLab

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¹Technische Universität Wien, Austria; ²Silvaco Europe Ltd., United Kingdom

Advanced Devices & VLSI Processing

Date: Wednesday, September 21, 2022

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Room: Aula 1F

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Defects & Traps Modeling

Date: Wednesday, September 21, 2022
Time: 9:20 - 10:50
Room: Aula 1D
Chair(s): Cristell Maneux, University of Bordeaux
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